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**PATENT APPLICATION**

**RESPONSE UNDER 37 CFR §1.116  
EXPEDITED PROCEDURE  
TECHNOLOGY CENTER ART UNIT 1675**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Takao ABE et al.

Group Art Unit: 1765

Application No.: 09/743,982

Examiner: M.A. Anderson

Filed: January 18, 2001

Docket No.: 108360

For: SILICON SINGLE CRYSTAL AND WAFER DOPED WITH GALLIUM AND  
METHOD FOR PRODUCING THEM

**AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR §1.116**

Director of the U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

In reply to the February 4, 2003 Office Action, please amend the above-identified  
application as follows:

**IN THE CLAIMS:**

Please replace claims 35-45 as follows:

35. (Twice Amended) The silicon single crystal solar cell according to Claim 30,

wherein loss of overall conversion efficiency due to photo-degradation is 0.5 % or less.

36. (Twice Amended) The silicon single crystal solar cell according to Claim 32,

wherein loss of overall conversion efficiency due to photo-degradation is 0.5 % or less.

37. (Twice Amended) A method for production of silicon single crystal to which

Ga is added according to Czochralski method wherein Ga is added in a silicon melt in a  
crucible, a seed crystal is brought into contact with the silicon melt and is pulled with rotating

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